Wilman Tsai

List of Publications by Year
in descending order

12	292	1163117 8	1281871 11
papers	citations	h-index	g-index

12	12	12	417
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Atomic layer deposition of hafnium oxide on germanium substrates. Journal of Applied Physics, 2005, 97, 064104.	2.5	95
2	The Fermi-level efficiency method and its applications on high interface trap density oxide-semiconductor interfaces. Applied Physics Letters, 2009, 94, .	3.3	50
3	Arsenic-dominated chemistry in the acid cleaning of InGaAs and InAlAs surfaces. Applied Physics Letters, 2008, 93, 194103.	3.3	39
4	Atomic Layer Deposition of Hafnium Oxide on Ge and GaAs Substrates: Precursors and Surface Preparation. Journal of the Electrochemical Society, 2008, 155, H937.	2.9	35
5	Materials Requirements of High-Speed and Low-Power Spin-Orbit-Torque Magnetic Random-Access Memory. IEEE Journal of the Electron Devices Society, 2020, 8, 674-680.	2.1	18
6	Large and robust charge-to-spin conversion in sputtered conductive WTe with disorder. Matter, 2021, 4, 1639-1653.	10.0	15
7	In-Situ Deposition of High-k Gate Stack on InGaAs and GaAs for Metal-Oxide-Semiconductor Devices with Low Equivalent Oxide Thickness. ECS Transactions, 2007, 11, 431-439.	0.5	13
8	The effects of wet surface clean and in situ interlayer on In0.52Al0.48As metal-oxide-semiconductor characteristics. Applied Physics Letters, 2010, 96, 142906.	3.3	8
9	CHALLENGES AND PROGRESS IN III-V MOSFETs FOR CMOS CIRCUITS. International Journal of High Speed Electronics and Systems, 2008, 18, 761-772.	0.7	7
10	Tunable spinâ€“orbit torque efficiency in in-plane and perpendicular magnetized [Pt/Co]n multilayer. Applied Physics Letters, 2021, 118, 042405.	3.3	5
11	Materials and Technologies for III-V MOSFETs. , 2010, , 195-250.		5
12	Spinâ€“orbit torques of an in-plane magnetized system modulated by the spin transport in the ferromagnetic Co layer. APL Materials, 2021, 9, .	5.1	2